

**Amendments to the Specification:**

Please replace the paragraph beginning at page 11, line 3  
with the following rewritten paragraph:

Figure 3 illustrates stage (a) in the manufacture of this embodiment. The substrate 40  
100 is typically of a low-cost insulating material (for example glass, or perhaps even an  
insulating polymer), having an insulating coating of, for example, silicon dioxide or silicon  
nitride providing its upper surface on which the circuit elements are formed. A silicon  
film 10 initially of amorphous material is deposited for the TFT islands and is crystallised  
in known manner by heating with a laser beam 200. Typically, an excimer laser may be  
used, with a laser energy and pulse rate sufficient to melt the film 10 through most of its  
thickness. The silicon film 10 typically reaches temperatures in the range of 1000°C to  
1400°C (depending on its hydrogen content) during this laser treatment.